

100V, 100A N-CHANNEL POWER MOSFET

GENERAL DESCRIPTION

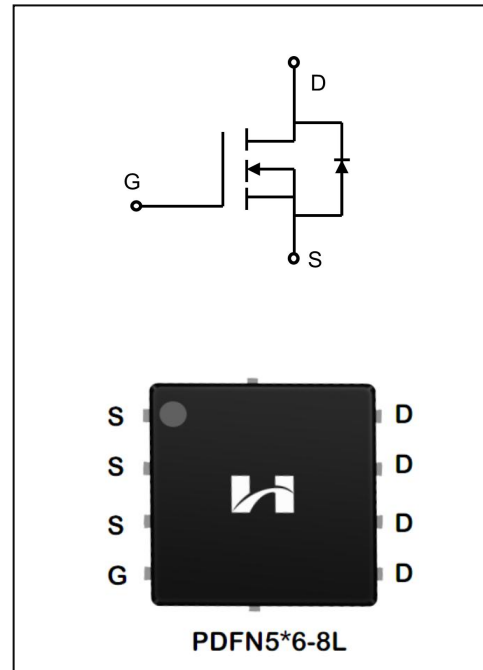
The SGM105R0T uses advanced SGT technology and design to provide excellent $R_{DS(on)}$ with low gate charge. It can be used in a wide variety applications.

Features

- ◆ $V_{DS}=100V, I_D=100A$
- ◆ $R_{DS(on)}$
 TYP: $3.9m\Omega$ @ $V_{GS}=10V$
 MAX: $5.0m\Omega$

Applications

- ◆ Power faction correction (PFC)
- ◆ Switched mode power supplies (SMPS)
- ◆ Uninterruptible power supply (UPS)
- ◆ LED lighting power



ORDERING INFORMATION

Part No.	Package	Marking	Material	Packing
SGM105R0T	PDFN5*6-8L	SGM105R0T	Pb Free	Reel

ABSOLUTE MAXIMUM RATINGS (T_J=25°C unless otherwise noted)

Characteristics		Symbol	Ratings	Unit
Drain-Source Voltage		V _{DS}	100	V
Gate-Source Voltage		V _{GS}	±20	V
Drain Current	T _C = 25°C	I _D	100	A
	T _C = 100°C		63	
Drain Current Pulsed(Note 1)		I _{DM}	400	A
Power Dissipation(T _C =25°C) -Derate above 25°C		P _D	132	W
Single Pulsed Avalanche Energy (Note 2)		E _{AS}	655	mJ
Operation Junction Temperature Range		T _J	-55~+150	°C
Storage Temperature Range		T _{stg}	-55~+150	°C
Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		TL	260	°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	MAX	Unit
Thermal Resistance, Junction-to-Case	R _{θJC}	0.95	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	50	°C/W

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain -Source Breakdown Voltage	B _{VDS}	V _{GS} =0V, I _D =250μA	100	--	--	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V	--	--	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =20V, V _{DS} =0V	--	--	100	nA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =-20V, V _{DS} =0V	--	--	-100	
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{GS} = V _{DS} , I _D =250μA	1.4	1.9	2.4	V
Static Drain- Source On State Resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =30A	--	5.2	7.5	mΩ
		V _{GS} =10V, I _D =40A	--	3.9	5.0	
Dynamic Characteristics						
Gate Resistance	R _g	V _{GS} =0V; f=1.0MHZ	--	3.0	--	Ω
Input Capacitance	C _{iss}	V _{DS} =50V V _{GS} =0V f=1.0MHZ	--	4740	--	pF
Output Capacitance	C _{oss}		--	618	--	
Reverse Transfer Capacitance	C _{rss}		--	21	--	
Switching Characteristics						
Turn-on Delay Time	t _{d(on)}	V _{DD} =50V, V _{DS} =10V R _G =3Ω; I _D =30A (Note 3.4)	--	21.2	--	ns
Turn-on Rise Time	t _r		--	78.6	--	
Turn-off Delay Time	t _{d(off)}		--	69.1	--	
Turn-off Fall Time	t _f		--	28.9	--	

Total Gate Charge	Q_g	$V_{DS}=50V, I_D=30A$ $V_{GS}=10V$ (Note 3.4)	--	68.1	--	nC
Gate-Source Charge	Q_{gs}		--	26.2	--	
Gate-Drain Charge	Q_{gd}		--	10.7	--	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Continuous Source Current	I_S	Integral Reverse P-N Junction Diode in the MOSFET	--	--	100	A
Pulsed Source Current	I_{SM}		--	--	400	
Diode Forward Voltage	V_{SD}	$I_S=40A, V_{GS}=0V$	--	0.82	1.4	V
Reverse Recovery Time	T_{rr}	$I_F=40A, V_R=10V,$ $dI_F/dt=100A/\mu S$	--	65	--	ns
Reverse Recovery Charge	Q_{rr}		--	82	--	nC

1. Pulse width limited by maximum junction temperature
2. $L=1mH, V_{DD}=50V, V_G=80V, R_G=25\Omega$, starting $T_J=25^\circ C$
3. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
4. Essentially independent of operating temperature

Typical Performance Characteristics

Figure 1. On-Region Characteristics

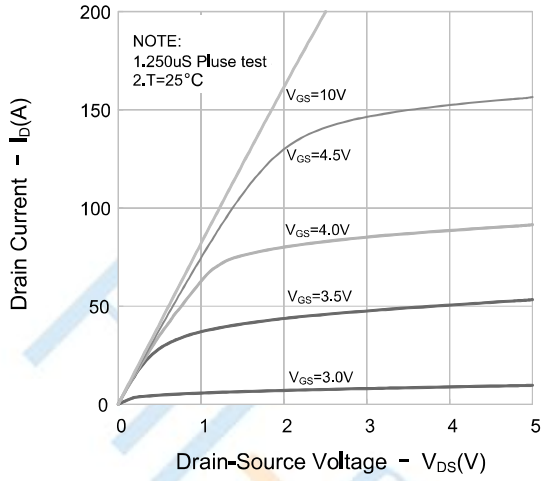


Figure 2. Transfer Characteristics

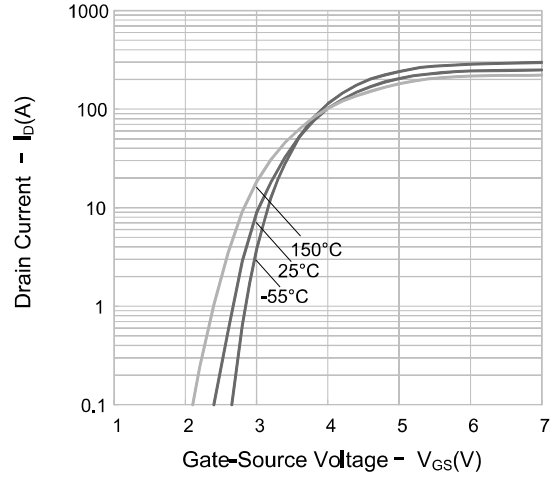


Figure 3. On-Resistance Variation vs. Drain Current

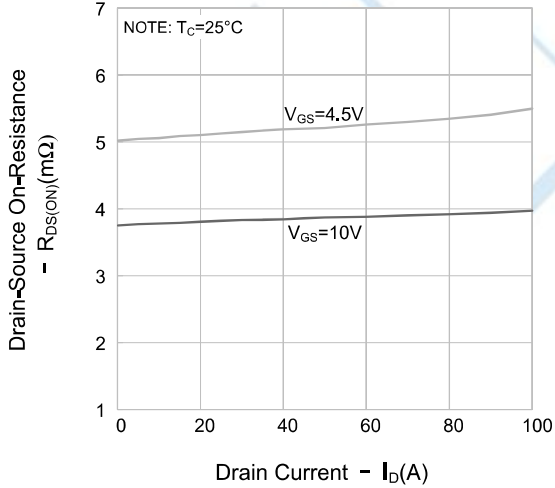


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

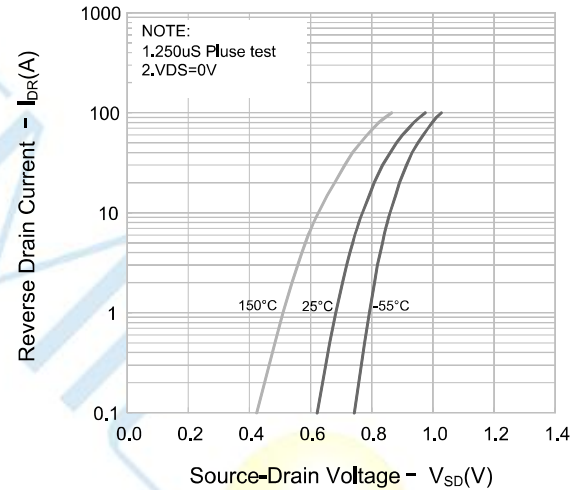


Figure 5. Capacitance Characteristics

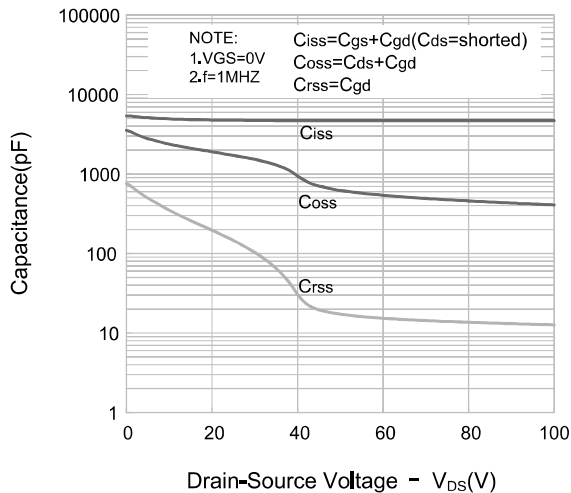
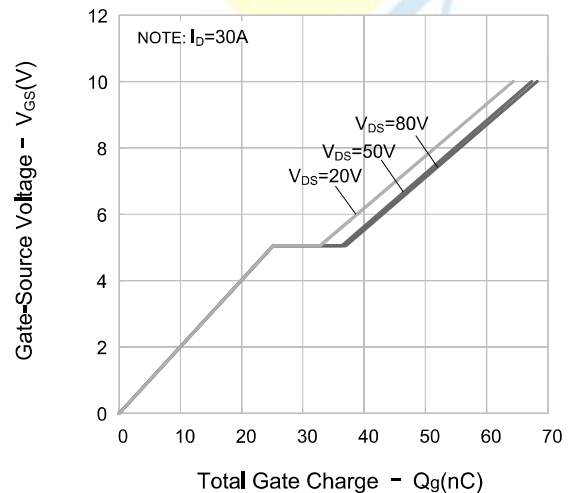


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics

Figure 7. Breakdown Voltage Variation vs. Temperature

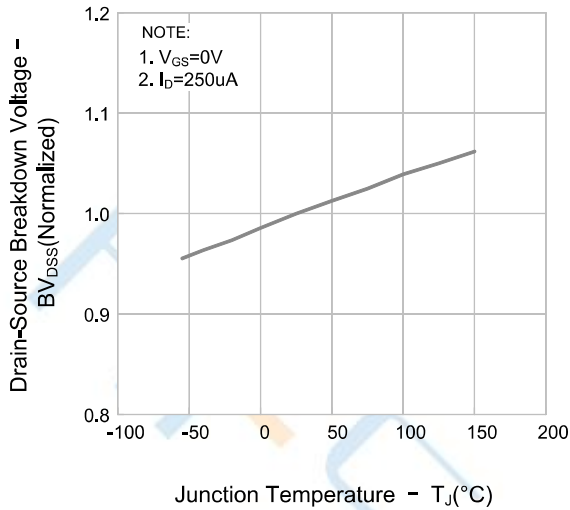


Figure 8. On-resistance Variation vs. Temperature

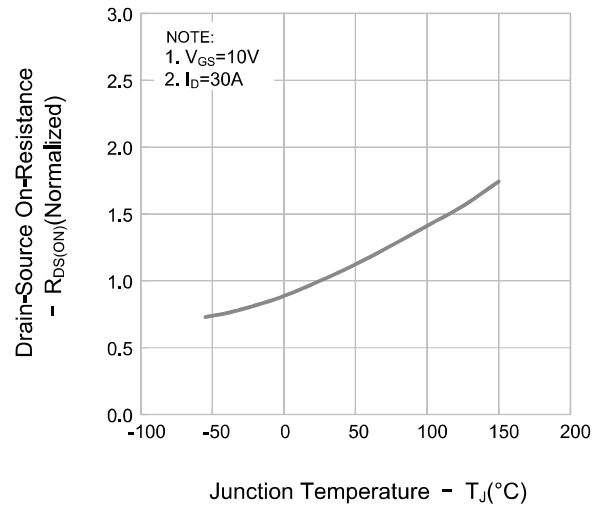
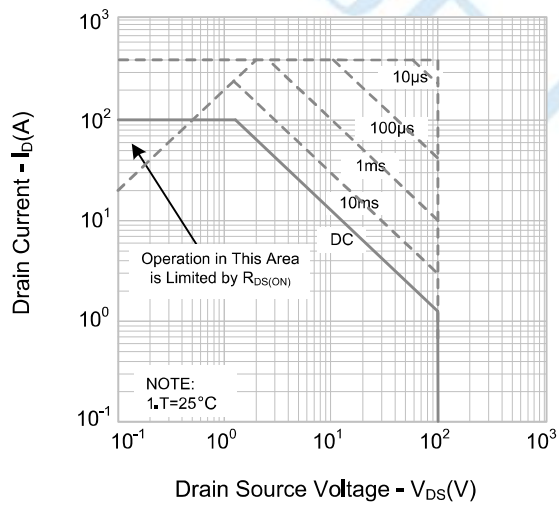
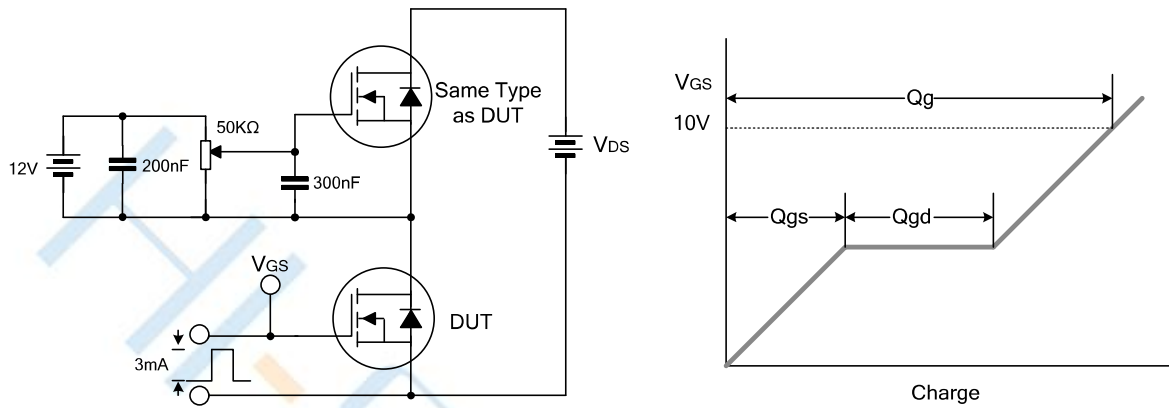


Figure 9. Max Safe Operating Area

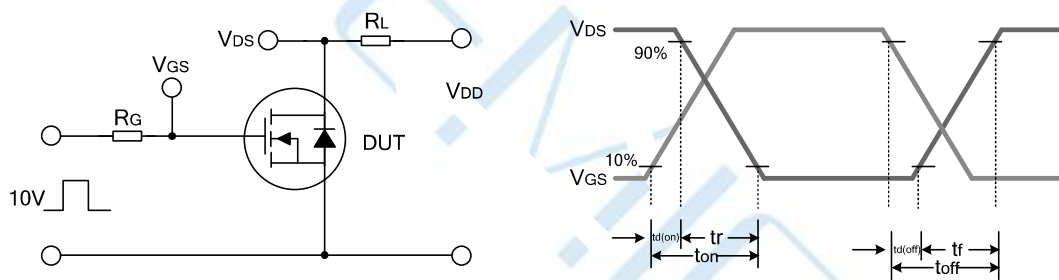


Test Circuit

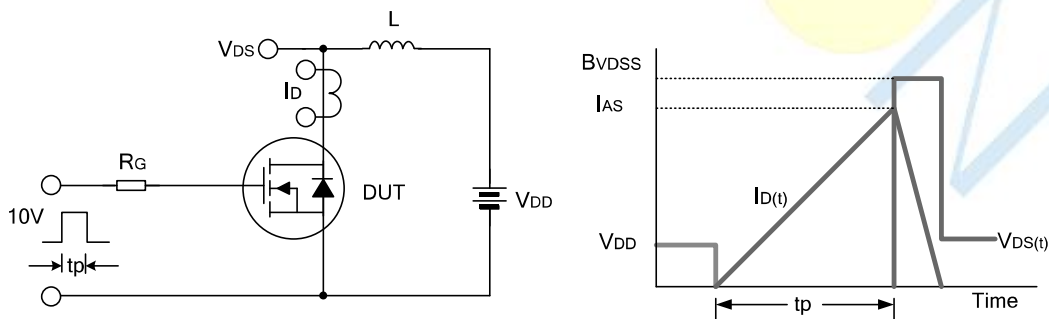
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveform

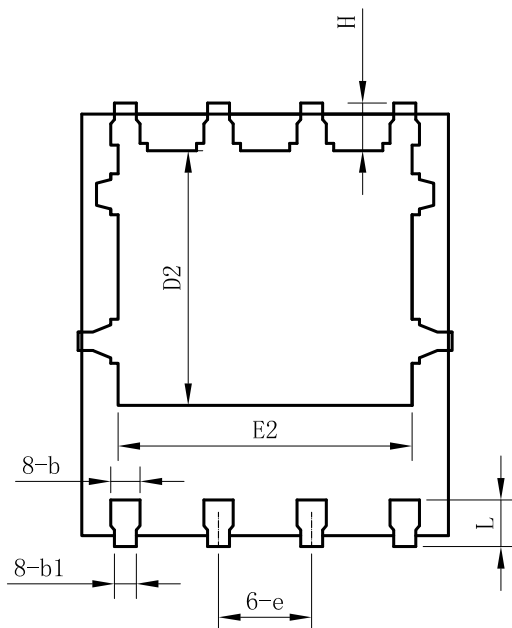
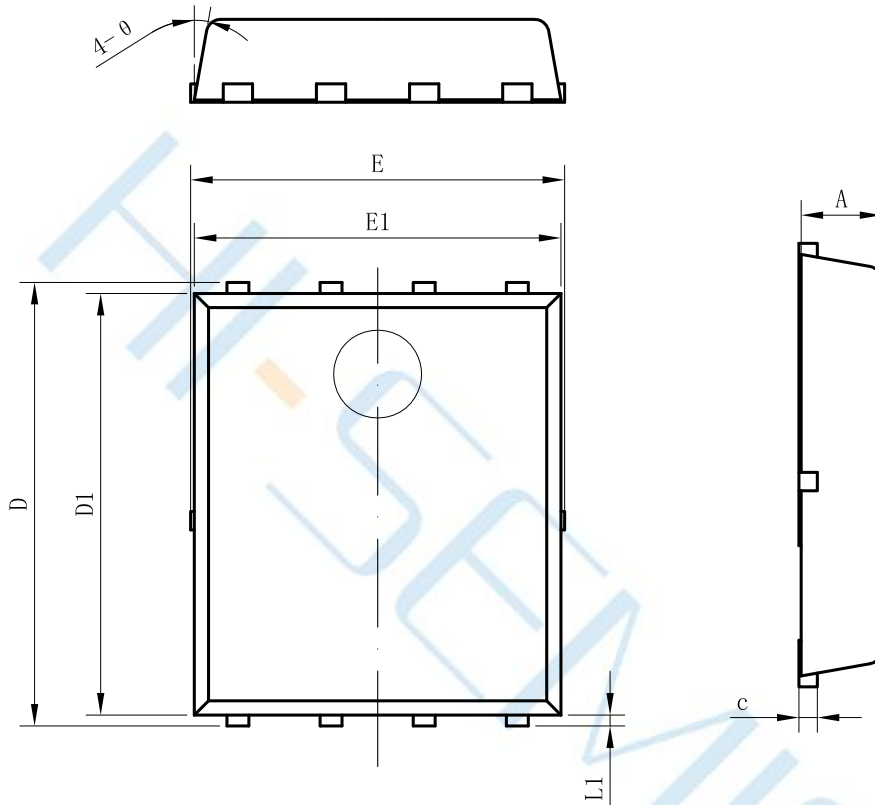


Undamped Inductive Switching Test Circuit & Waveform



Package Dimensions of PDFN5*6-8L

Unit:mm



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	1.0	1.1	1.2
b	0.35	0.4	0.45
b1		(0.3)	
c	0.2	0.25	0.35
D	5.9	6.05	6.2
D1	5.65	5.75	5.85
D2		(3.475)	
E			5.2
E1	4.9	5	5.1
E2		(4.01)	
e		1.27BSC	
H	0.5	0.65	0.75
L	0.51	0.635	0.75
L1		0.15	
θ		10°	

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